Dual 150 mA, Low I_Q, Low **Dropout Voltage Regulator**

The NCV8152 is 150 mA, Dual Output Linear Voltage Regulator. Device provides a very stable and accurate voltage with ultra low noise and very high Power Supply Rejection Ratio (PSRR) suitable for RF applications. The NCV8152 is suitable for powering RF blocks of automotive infotainment systems and other power sensitive device. Due to low power consumption the NCV8152 offers high efficiency and low thermal dissipation.

Features

- Operating Input Voltage Range: 1.9 V to 5.25 V
- Two Independent Output Voltages: (for details please refer to the Ordering Information section)
- Very Low Dropout: 150 mV Typical at 150 mA
- Low IQ of typ. 50 μA per Channel
- High PSRR: 75 dB at 1 kHz
- Two Independent Enable Pins
- Thermal Shutdown and Current Limit Protections
- Stable with a 0.22 µF Ceramic Output Capacitor
- Available in XDFN6 1.2 x 1.2 mm Package
- Active Output Discharge for Fast Output Turn-Off
- NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These are Pb-Free Devices

Typical Applications

- Wireless LAN, Bluetooth®, ZigBee® Interfaces
- Parking Camera Modules
- Automotive Infotainment Systems



ON Semiconductor®

http://onsemi.com

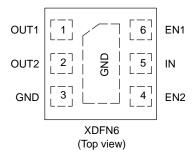






= Specific Device Code = Date Code

PIN CONNECTIONS



ORDERING INFORMATION

See detailed ordering and shipping information on page 16 of this data sheet

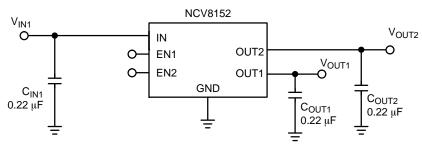


Figure 1. Typical Application Schematic

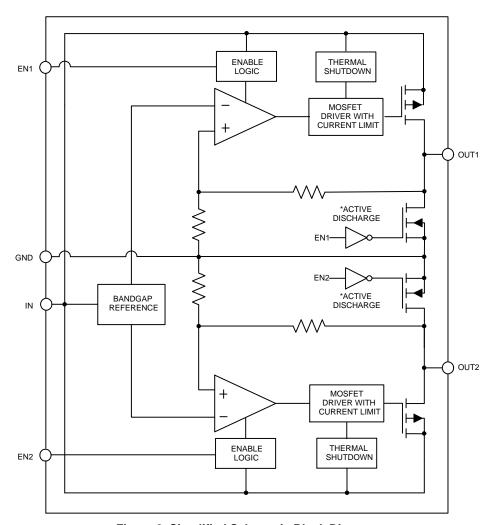


Figure 2. Simplified Schematic Block Diagram

PIN FUNCTION DESCRIPTION

Pin No. XDFN6	Pin Name	Description
1	OUT1	Regulated output voltage of the first channel. A small 0.22 µF ceramic capacitor is needed from this pin to ground to assure stability.
2	OUT2	Regulated output voltage of the second channel. A small 0.22 μF ceramic capacitor is needed from this pin to ground to assure stability.
3	GND	Power supply ground. Soldered to the copper plane allows for effective heat dissipation.
4	EN2	Driving EN2 over 0.9 V turns–on OUT2. Driving EN below 0.4 V turns–off the OUT2 and activates the active discharge.
5	IN	Input pin common for both channels. It is recommended to connect 0.22 μF ceramic capacitor close to the device pin.
6	EN1	Driving EN1 over 0.9 V turns–on OUT1. Driving EN below 0.4 V turns–off the OUT1 and activates the active discharge.
_	EP	Exposed pad must be tied to ground. Soldered to the copper plane allows for effective thermal dissipation.

ABSOLUTE MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Input Voltage (Note 1)	V _{IN}	−0.3 V to 6 V	V
Output Voltage	V _{OUT1} , V _{OUT2}	-0.3 V to VIN + 0.3 V or 6 V	V
Enable Inputs	V _{EN1} , V _{EN2}	-0.3 V to VIN + 0.3 V or 6 V	V
Output Short Circuit Duration	t _{SC}	Indefinite	S
Maximum Junction Temperature	$T_{J(MAX)}$	125	°C
Storage Temperature	T _{STG}	-55 to 150	°C
ESD Capability, Human Body Model (Note 2)	ESD _{HBM}	2000	V
ESD Capability, Machine Model (Note 2)	ESD _{MM}	200	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- Refer to ELECTRICAL CHARACTERISTIS and APPLICATION INFORMATION for Safe Operating Area.
 This device series incorporates ESD protection and is tested by the following methods:
- - ESD Human Body Model tested per EIA/JESD22-A114
 - ESD Machine Model tested per EIA/JESD22-A115
 - Latchup Current Maximum Rating tested per JEDEC standard: JESD78.

THERMAL CHARACTERISTICS (Note 3)

Rating	Symbol	Value	Unit
Thermal Characteristics, XDFN6 1.2 x 1.2 mm, Thermal Resistance, Junction–to–Air Thermal Characterization Parameter, Junction–to–Lead (Pin 2)	θJA θJL	170	°C/W

3. Single component mounted on 1 oz, FR4 PCB with 645mm2 Cu area.

ELECTRICAL CHARACTERISTIC

 $-40^{\circ}C \leq T_{J} \leq 125^{\circ}C; \ V_{IN} = V_{OUT(NOM)} + 1 \ V \ or \ 2.5 \ V, \ whichever \ is \ greater; \ V_{EN} = 0.9 \ V, \ I_{OUT} = 1 \ mA, \ C_{IN} = C_{OUT} = 0.22 \ \mu F. \ Typical values are at \ T_{J} = +25^{\circ}C. \ Min/Max \ values \ are specified for \ T_{J} = -40^{\circ}C \ and \ T_{J} = 125^{\circ}C \ respectively. \ (Note 4)$

Parameter	Test Condi	Symbol	Min	Тур	Max	Unit	
Operating Input Voltage			Vin	1.9		5.25	V
Output Voltage Accuracy	4000 x T x 40500	V _{OUT} > 2 V	Vout	-2.8		+2.8	%
	$-40^{\circ}\text{C} \le \text{T}_{\text{J}} \le 125^{\circ}\text{C}$	V _{OUT} ≤ 2 V		-80		+80	mV
Line Regulation	Vout + 0.5 V or 2.5 V ≤ VIN ≤	5 V	Reg _{LINE}		0.02	0.1	%/V
Load Regulation	IOUT = 1 mA to 150 mA		Reg _{LOAD}		15	50	mV
		V _{OUT(nom)} = 1.8 V			270	420	
Dropout Voltage (Note 5)	I _{out} = 150 mA	V _{OUT(nom)} = 3.0 V	V_{DO}		150	240	mV
		V _{OUT(nom)} = 3.3 V			140	240	
Output Current Limit	V _{OUT} = 90% V _{OUT(nom)}		ICL	150			mA
Quiescent Current	$IOUT = 0$ mA, $EN1 = V_{IN}$, $EN2 = 0$ V or $EN2 = V_{IN}$, $EN1 = 0$ V		lQ		50	100	μΑ
	IOUT1 = IOUT2 = 0 mA, V _{EN1} =	ΙQ		85	200	μΑ	
Shutdown current (Note 6)	$Ven \le 0.4 \text{ V}, V_{IN} = 5.25 \text{ V}$		Idis		0.1	1	μΑ
EN Pin Threshold Voltage High Threshold Low Threshold	VEN Voltage increasing VEN Voltage decreasing			0.9		0.4	V
EN Pin Input Current	VEN = VIN = 5.25 V		len		0.3	1.0	μΑ
Power Supply Rejection Ratio	$VIN = VOUT+1 V for VOUT > 2 V for VOUT \le 2 V, IOUT = 10 mA$	PSRR		75		dB	
Output Noise Voltage	f = 10 Hz to 100 kHz	Vn		75		μV_{rms}	
Active Discharge Resistance	ive Discharge Resistance $V_{IN} = 4 \text{ V}, V_{EN} < 0.4 \text{ V}$				50		Ω
Thermal Shutdown Temperature	Temperature increasing from T _J = +25°C				160		°C
Thermal Shutdown Hysteresis Temperature falling from Tsb			Tsdh	-	20	-	°C

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Performance guaranteed over the indicated operating temperature range by design and/or characterization. Production tested at T_J = T_A = 25°C. Low duty cycle pulse techniques are used during testing to maintain the junction temperature as close to ambient as possible.

^{5.} Characterized when V_{OUT} falls 100 mV below the regulated voltage at $V_{IN} = V_{OUT(NOM)} + 1$ V. 6. Shutdown Current is the current flowing into the IN pin when the device is in the disable state.

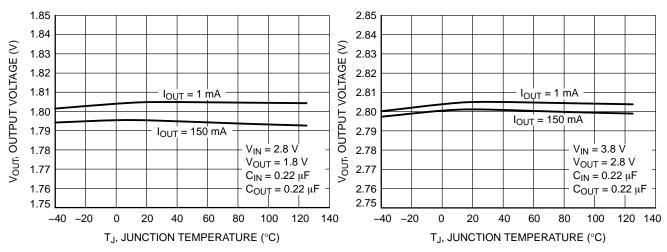


Figure 3. Output Voltage vs. Temperature $V_{OUT} = 1.8 \text{ V}$

Figure 4. Output Voltage vs. Temperature $V_{OUT} = 2.8 \text{ V}$

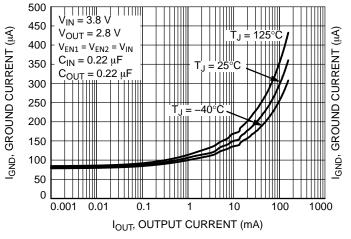


Figure 5. Ground Current vs. Output Current –
One Channel Load

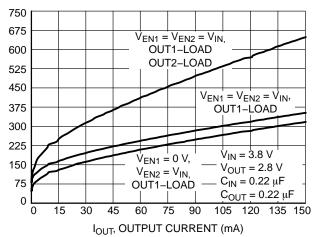


Figure 6. Ground Current vs. Output Current –
Different Load Combinations

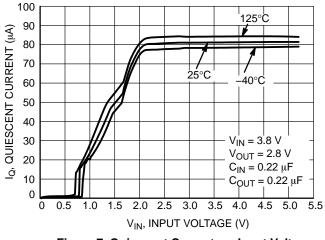


Figure 7. Quiescent Current vs. Input Voltage– Both Outputs ON

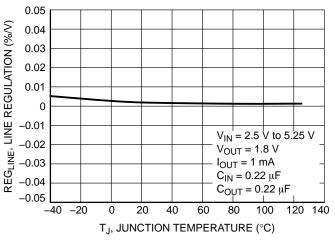


Figure 8. Line Regulation vs. Temperature $V_{OUT} = 1.8 \text{ V}$

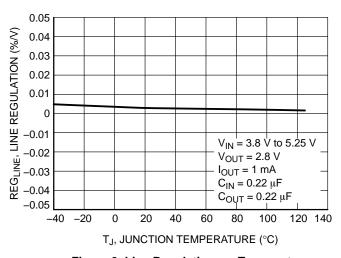


Figure 9. Line Regulation vs. Temperature $V_{OUT} = 2.8 \text{ V}$

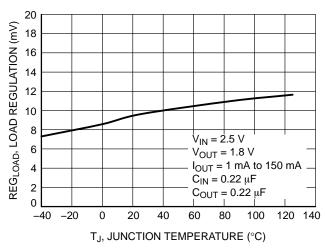


Figure 10. Load Regulation vs. Temperature $V_{OUT} = 1.8 \text{ V}$

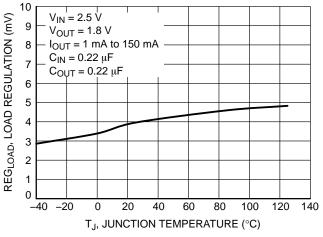


Figure 11. Load Regulation vs. Temperature V_{OUT} = 2.8 V

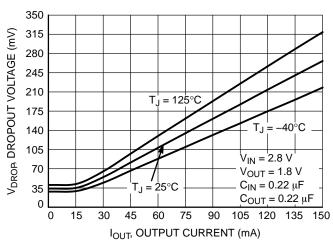


Figure 12. Dropout Voltage vs. Output Current $V_{OUT} = 1.8 \text{ V}$

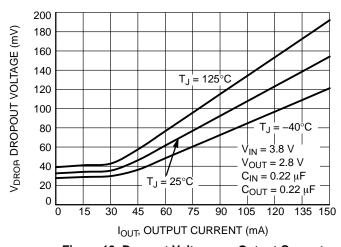


Figure 13. Dropout Voltage vs. Output Current $V_{OUT} = 2.8 \text{ V}$

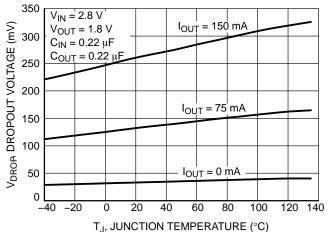


Figure 14. Dropout Voltage vs. Temperature $V_{OUT} = 1.8 \text{ V}$

TYPICAL CHARACTERISTICS

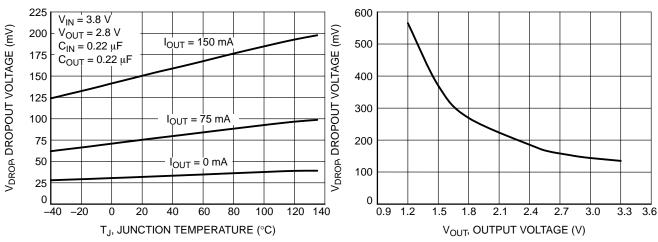


Figure 15. Dropout Voltage vs. Temperature $V_{OUT} = 2.8 V$

Figure 16. Dropout Voltage vs. Output Voltage

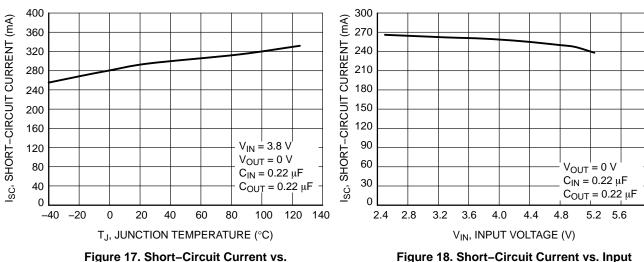


Figure 17. Short-Circuit Current vs. **Temperature**

200

180

160

140 120

100

80

60

40

20

-40 -20

I_{DIS}, DISABLE CURRENT (nA)

1.0 0.9 ENABLE VOLTAGE (V) 0.8 ÒFF –> ON 0.7 0.6 ÖΝ −> OFF 0.5 0.4 $V_{IN} = 5.5 \text{ V}$ 0.3 $V_{IN} = 3.8 \text{ V}$ $V_{OUT} = 2.8 V$ V_{EN}, 0.2 V_{OUT} = 2.8 V $C_{IN} = 0.22 \, \mu F$ $C_{IN} = 0.22 \, \mu F$ $C_{OUT} = 0.22 \mu F$ 0.1 $C_{OUT} = 0.22 \mu F$ 100 120 140 -40 -20 100 120 140 40 60 T_J, JUNCTION TEMPERATURE (°C) T_J, JUNCTION TEMPERATURE (°C)

Figure 19. Disable Current vs. Temperature

60

80

40

Figure 20. Enable Voltage Threshold vs. **Temperature**

Voltage

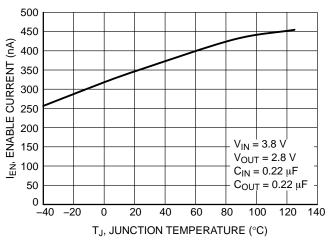


Figure 21. Current to Enable Pin vs. Temperature

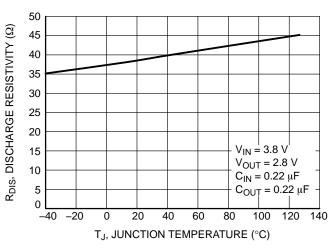


Figure 22. Discharge Resistance vs. Temperature

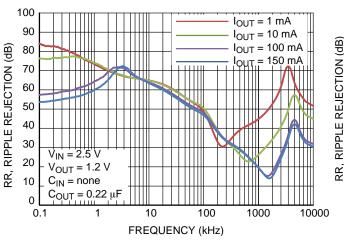


Figure 23. Power Supply Rejection Ratio, V_{OUT} = 1.2 V, C_{OUT} = 0.22 μF

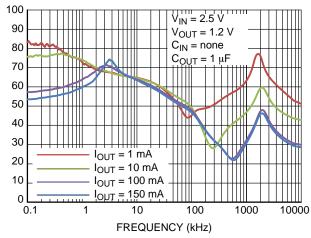


Figure 24. Power Supply Rejection Ratio, $V_{OUT} = 1.2 \text{ V, } C_{OUT} = 1 \mu F$

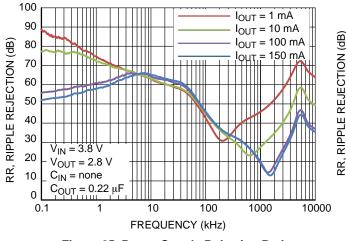


Figure 25. Power Supply Rejection Ratio, V_{OUT} = 2.8 V, C_{OUT} = 0.22 μF

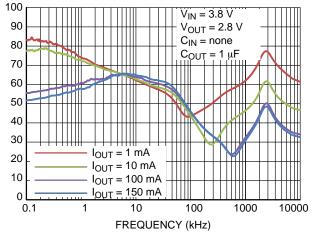
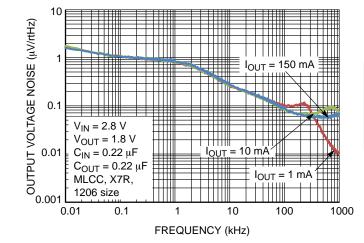
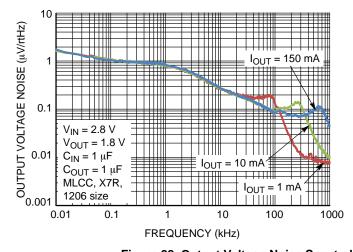


Figure 26. Power Supply Rejection Ratio, $V_{OUT} = 2.8 \text{ V}, C_{OUT} = 1 \mu\text{F}$



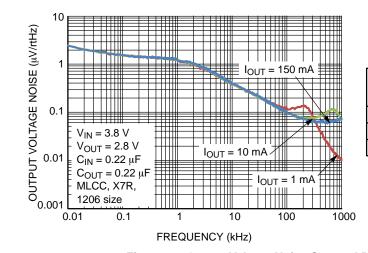
	RMS Output Noise (μV)		
I _{OUT}	10 Hz – 100 kHz	100 Hz – 100 kHz	
1 mA	68.07	67.07	
10 mA	67.30	66.31	
150 mA	69.74	68.80	

Figure 27. Output Voltage Noise Spectral Density for $V_{OUT} = 1.8 \text{ V}$, $C_{OUT} = 220 \text{ nF}$



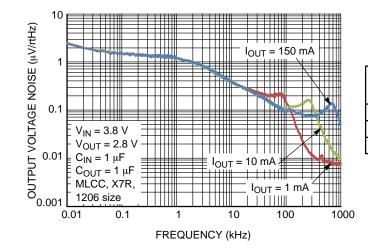
	RMS Output Noise (μV)			
l _{OUT}	10 Hz – 100 kHz	100 Hz – 100 kHz		
1 mA	76.23	75.33		
10 mA	67.12	66.12		
150 mA	69.06	68.12		

Figure 28. Output Voltage Noise Spectral Density for V_{OUT} = 1.8 V, C_{OUT} = 1 μF



	RMS Output Noise (μV)			
lout	10 Hz – 100 kHz	100 Hz – 100 kHz		
1 mA	93.42	91.99		
10 mA	92.88	91.45		
150 mA	94.67	93.26		

Figure 29. Output Voltage Noise Spectral Density for V_{OUT} = 2.8 V, C_{OUT} = 220 nF



	RMS Output Noise (μV)		
I _{OUT}	10 Hz – 100 kHz	100 Hz – 100 kHz	
1 mA	102.14	100.86	
10 mA	93.03	91.59	
150 mA	94.74	93.12	

Figure 30. Output Voltage Noise Spectral Density for V_{OUT} = 2.8 V, C_{OUT} = 1 μF

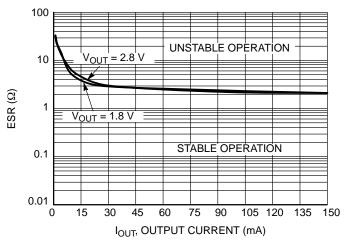


Figure 31. Output Capacitor ESR vs. Output Current

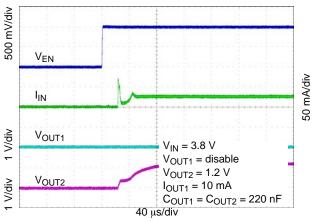


Figure 32. Enable Turn-on Response – VR1 = Off, VR2 = 10 mA

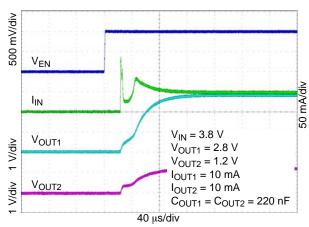


Figure 33. Enable Turn-on Response – VR1 = 10 mA, VR2 = 10 mA

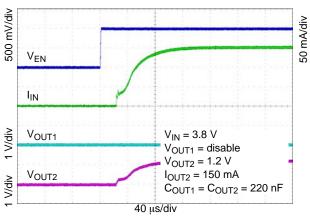


Figure 34. Enable Turn-on Response – VR1 = Off, VR2 = 150 mA

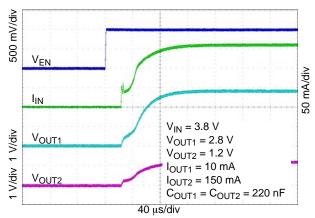


Figure 35. Enable Turn-on Response – VR1 = 10 mA, VR2 = 150 mA

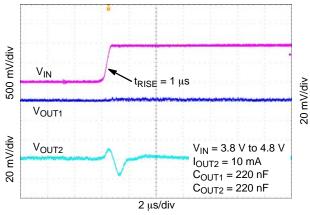


Figure 36. Line Transient Response – Rising Edge, V_{EN1} = 0 V, V_{EN2} = V_{IN} , V_{OUT2} = 3.3 V, I_{OUT2} = 10 mA

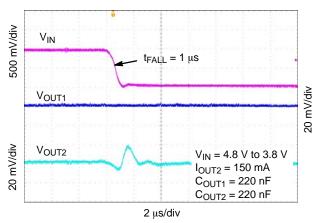


Figure 37. Line Transient Response – Falling Edge, V_{EN1} = 0 V, V_{EN2} = V_{IN} , V_{OUT2} = 3.3 V, I_{OUT2} = 10 mA

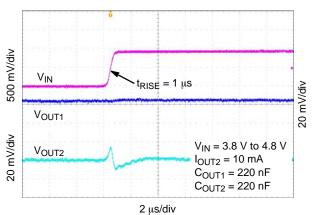


Figure 38. Line Transient Response – Rising Edge, V_{EN1} = 0 V, V_{EN2} = V_{IN} , V_{OUT2} = 3.3 V, I_{OUT2} = 150 mA

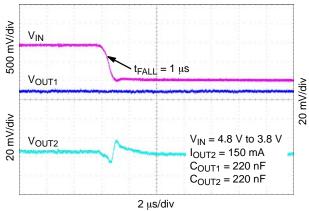


Figure 39. Line Transient Response – Falling Edge, V_{EN1} = 0 V, V_{EN2} = V_{IN} , V_{OUT2} = 3.3 V, I_{OUT2} = 150 mA

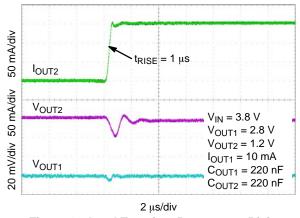


Figure 40. Load Transient Response – Rising Edge, I_{OUT} = 1 mA to 150 mA

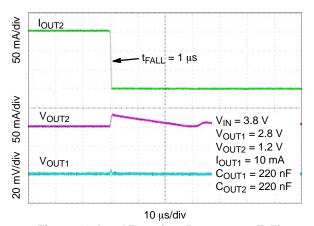


Figure 41. Load Transient Response – Falling Edge, I_{OUT} = 150 mA to 1 mA

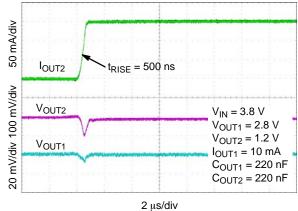


Figure 42. Load Transient Response – Rising Edge, I_{OUT} = 0.1 mA to 150 mA

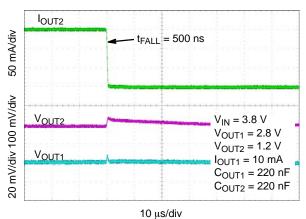


Figure 43. Load Transient Response – Falling Edge, I_{OUT} = 150 mA to 0.1 mA

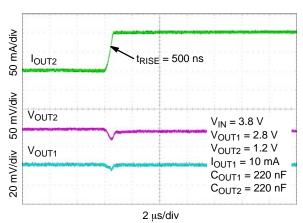


Figure 44. Load Transient Response – Rising Edge, I_{OUT} = 50 mA to 150 mA

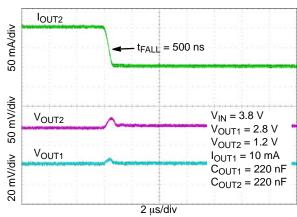


Figure 45. Load Transient Response – Falling Edge, I_{OUT} = 150 mA to 50 mA

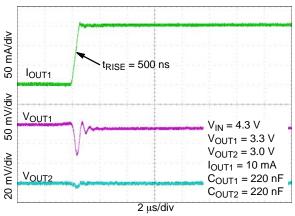


Figure 47. Load Transient Response – Rising Edge, I_{OUT} = 1 mA to 150 mA

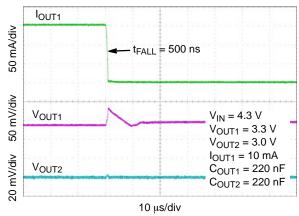


Figure 48. Load Transient Response – Falling Edge, I_{OUT} = 150 mA to 1 mA

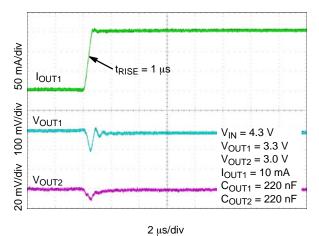
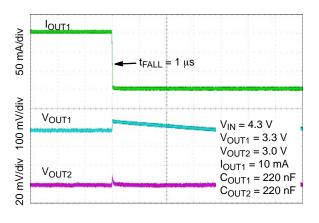


Figure 46. Load Transient Response – Rising Edge, I_{OUT} = 0.1 mA to 150 mA



20 μs/div Figure 49. Load Transient Response – Falling Edge, I_{OUT} = 150 mA to 0.1 mA

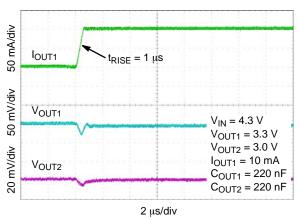


Figure 50. Load Transient Response – Rising Edge, I_{OUT} = 50 mA to 150 mA

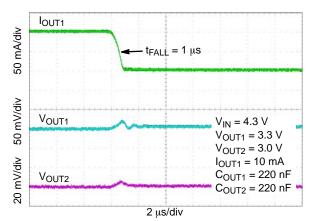


Figure 51. Load Transient Response – Falling Edge, I_{OUT} = 150 mA to 50 mA

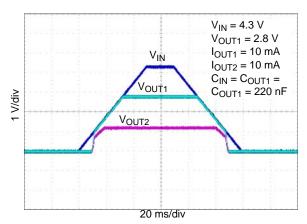


Figure 52. Turn-on/off - Slow Rising VIN

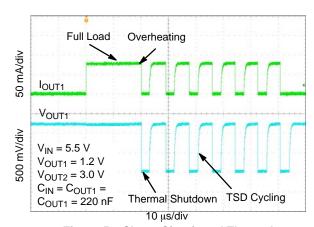


Figure 53. Short-Circuit and Thermal Shutdown

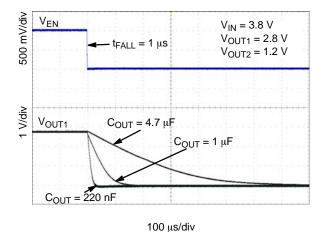


Figure 54. Enable Turn-off

APPLICATIONS INFORMATION

General

The NCV8152 is a dual output high performance 150 mA Low Dropout Linear Regulator. This device delivers very high PSRR (75 dB at 1 kHz) and excellent dynamic performance as load/line transients. In connection with low quiescent current this device is very suitable for various battery powered applications such as tablets, cellular phones, wireless and many others. Each output is fully protected in case of output overload, output short circuit condition and overheating, assuring a very robust design. The NCV8152 device is housed in XDFN-6 1.2 mm x 1.2 mm package which is useful for space constrains application.

Input Capacitor Selection (CIN)

It is recommended to connect at least a 0.22 μF Ceramic X5R or X7R capacitor as close as possible to the IN pin of the device. This capacitor will provide a low impedance path for unwanted AC signals or noise modulated onto constant input voltage. There is no requirement for the min. or max. ESR of the input capacitor but it is recommended to use ceramic capacitors for their low ESR and ESL. A good input capacitor will limit the influence of input trace inductance and source resistance during sudden load current changes. Larger input capacitor may be necessary if fast and large load transients are encountered in the application.

Output Decoupling (COUT)

The NCV8152 requires an output capacitor for each output connected as close as possible to the output pin of the regulator. The recommended capacitor value is $0.22~\mu F$ and X7R or X5R dielectric due to its low capacitance variations over the specified temperature range. The NCV8152 is designed to remain stable with minimum effective capacitance of $0.15~\mu F$ to account for changes with temperature, DC bias and package size. Especially for small package size capacitors such as 0201 the effective capacitance drops rapidly with the applied DC bias.

There is no requirement for the minimum value of Equivalent Series Resistance (ESR) for the C_{OUT} but the maximum value of ESR should be less than 2 Ω . Larger output capacitors and lower ESR could improve the load transient response or high frequency PSRR. It is not recommended to use tantalum capacitors on the output due to their large ESR. The equivalent series resistance of tantalum capacitors is also strongly dependent on the temperature, increasing at low temperature.

Enable Operation

The NCV8152 uses the dedicated EN pin for each output channel. This feature allows driving outputs separately.

If the EN pin voltage is <0.4 V the device is guaranteed to be disabled. The pass transistor is turned—off so that there is virtually no current flow between the IN and OUT. The active discharge transistor is active so that the output voltage V_{OUT} is pulled to GND through a 50 Ω resistor. In the

disable state the device consumes as low as typ. 10 nA from the $V_{\rm IN}$.

If the EN pin voltage >0.9 V the device is guaranteed to be enabled. The NCV8152 regulates the output voltage and the active discharge transistor is turned—off.

The both EN pin has internal pull-down current source with typ. value of 300 nA which assures that the device is turned-off when the EN pin is not connected. In the case where the EN function isn't required the EN should be tied directly to IN.

Output Current Limit

Output Current is internally limited within the IC to a typical 280 mA. The NCV8152 will source this amount of current measured with a voltage drops on the 90% of the nominal V_{OUT} . If the Output Voltage is directly shorted to ground ($V_{OUT} = 0$ V), the short circuit protection will limit the output current to 300 mA (typ). The current limit and short circuit protection will work properly over whole temperature range and also input voltage range. There is no limitation for the short circuit duration. This protection works separately for each channel. Short circuit on the one channel do not influence second channel which will work according to specification.

Thermal Shutdown

When the die temperature exceeds the Thermal Shutdown threshold ($T_{SD}-160^{\circ}\text{C}$ typical), Thermal Shutdown event is detected and the affected channel is turn–off. Second channel still working. The channel which is overheated will remain in this state until the die temperature decreases below the Thermal Shutdown Reset threshold ($T_{SDU}-140^{\circ}\text{C}$ typical). Once the device temperature falls below the 140°C the appropriate channel is enabled again. The thermal shutdown feature provides the protection from a catastrophic device failure due to accidental overheating. This protection is not intended to be used as a substitute for proper heat sinking. The long duration of the short circuit condition to some output channel could cause turn–off other output when heat sinking is not enough and temperature of the other output reach T_{SD} temperature.

Power Dissipation

As power dissipated in the NCV8152 increases, it might become necessary to provide some thermal relief. The maximum power dissipation supported by the device is dependent upon board design and layout. Mounting pad configuration on the PCB, the board material, and the ambient temperature affect the rate of junction temperature rise for the part.

The maximum power dissipation the NCV8152 can handle is given by:

$$P_{D(MAX)} = \frac{\left[125^{\circ}C - T_{A}\right]}{\theta_{JA}}$$
 (eq. 1)

The power dissipated by the NCV8152 for given application conditions can be calculated from the following equations:

$$\begin{split} P_{D} \approx V_{IN} \times I_{GND} + I_{OUT1} & \left(V_{IN} - V_{OUT1} \right) \\ & + I_{OUT2} & \left(V_{IN} - V_{OUT2} \right) \end{split} \tag{eq. 2}$$

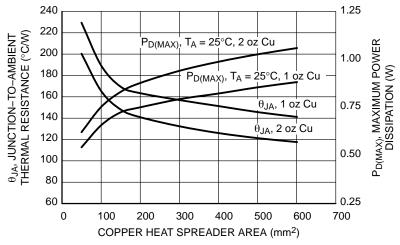


Figure 55. θ_{JA} vs. Copper Area (XDFN-6)

Reverse Current

The PMOS pass transistor has an inherent body diode which will be forward biased in the case that $V_{OUT} > V_{IN}$. Due to this fact in cases, where the extended reverse current condition can be anticipated the device may require additional external protection.

Power Supply Rejection Ratio

The NCV8152 features very good Power Supply Rejection ratio. If desired the PSRR at higher frequencies in the range 100 kHz - 10 MHz can be tuned by the selection of C_{OUT} capacitor and proper PCB layout.

Turn-On Time

The turn–on time is defined as the time period from EN assertion to the point in which V_{OUT} will reach 98% of its

nominal value. This time is dependent on various application conditions such as $V_{OUT(NOM)}$, C_{OUT} , T_A .

PCB Layout Recommendations

To obtain good transient performance and good regulation characteristics place input and output capacitors close to the device pins and make the PCB traces wide. In order to minimize the solution size, use 0402 capacitors. Larger copper area connected to the pins will also improve the device thermal resistance. The actual power dissipation can be calculated from the equation above (Equation 2). Expose pad should be tied the shortest path to the GND pin.

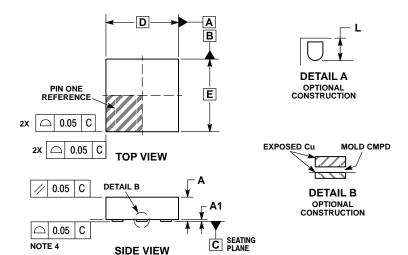
ORDERING INFORMATION

Device	Voltage Option (OUT1/OUT2)	Marking	Marking Rotation	Package	Shipping [†]
NCV8152MX300180TCG	3.0 V/1.8 V	L	90°	XDFN-6	3000 / Tape & Reel
NCV8152MX330180TCG	3.3 V/1.8 V	R	90°	(Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

XDFN6 1.2x1.2, 0.4P CASE 711AT ISSUE O

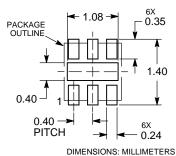


NOTES:

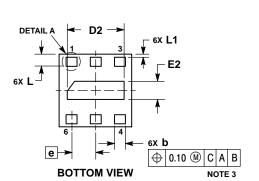
- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. DIMENSION b APPLIES TO PLATED
- DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.25mm FROM TERMINAL TIPS.
- COPLANARITY APPLIES TO THE PAD AS WELL AS THE TERMINALS.

	MILLIMETERS			
DIM	MIN	MAX		
Α	0.30	0.45		
A1	0.00	0.05		
b	0.13	0.23		
D	1.20 BSC			
D2	0.84	1.04		
E	1.20 BSC			
E2	0.20	0.40		
е	0.40 BSC			
L	0.15	0.25		
L1	0.05 REF			

RECOMMENDED MOUNTING FOOTPRINT*



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



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